

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	brandon near erik.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:16
L2	2045681	(dielectric or insulat\$3) ad (substrate or wafer) and (polymer near3 composite) and (drain) and (source) and (organic near3 layer) and (channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:18
L3	16	(dielectric or insulat\$3) and (substrate or wafer) and (polymer near3 composite) and (drain) and (source) and (organic near3 layer) and (channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:21
L4	72	(dielectric or insulat\$3) and (substrate or wafer) and (polymer near3 composite) and (drain) and (source) and (organic near3 layer) and (channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:21
L5	63	(dielectric) and (substrate or wafer) and (polymer near3 composite) and (drain) and (source) and (organic near3 layer) and (channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:46
L6	51	(dielectric) and (substrate or wafer) and (polymer near composite) and (drain) and (source) and (organic near3 layer) and (channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:22
L7	47	6 and (organic) with (polymer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:22
L8	38	7 and (dielectric) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:23
L9	29	8 and (polymer) with (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:35

L10	2007	(organic) with (polythiophene)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:35
L11	889	(organic) with (polythiophene) with (polymer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:38
L12	3	11 and (method) with (active near device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:39
L13	86	(dielectric) and (substrate or wafer) and (polymer near3 composite) and (drain) and (source) and (organic near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:53
L14	3370	(dielectric) and (substrate or wafer) and (drain) and (source) and (organic near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:58
L15	0	14 and (dissov\$3) with (solution)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:59
L16	0	14 and (dissov\$3) with (solvent)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:59
L17	570	14 and (dissolv\$3) with (solvent or solution)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 17:59
L18	356	14 and (dissolv\$3) with (solution)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:00
L19	351	18 and (method)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:00

L20	177440	"438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:01
L21	113	19 and 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:16
L22	2246	438/586.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:01
L23	1	21 and 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:01
L24	27	21 and (polymer) near25 (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 18:32